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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	11000
Number of Logic Elements/Cells	44000
Total RAM Bits	1990656
Number of I/O	245
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	554-FBGA
Supplier Device Package	554-CABGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5um5g-45f-8bg554c

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2.2.2. Modes of Operation

Slices 0-2 have up to four potential modes of operation: Logic, Ripple, RAM and ROM. Slice 3 is not needed for RAM mode, it can be used in Logic, Ripple, or ROM modes.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note that LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
 - A greater-than-or-equal-to B
 - A not-equal-to B
 - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed in one PFU using each LUT block in Slice 0 and Slice 1 as a 16 x 2-bit memory in each slice. Slice 2 is used to provide memory address and control signals.

A 16 x 2-bit pseudo dual port RAM (PDPR) memory is created in one PFU by using one Slice as the read-write port and the other companion slice as the read-only port. The slice with the read-write port updates the SRAM data contents in both slices at the same write cycle.

ECP5/ECP5-5G devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. [Table 2.3](#) lists the number of slices required to implement different distributed RAM primitives. For more information about using RAM in ECP5/ECP5-5G devices, refer to [ECP5 and ECP5-5G Memory Usage Guide \(TN1264\)](#).

Table 2.3. Number of Slices Required to Implement Distributed RAM

	SPR 16 X 4	PDPR 16 X 4
Number of slices	3	6

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

ROM Mode

ROM mode uses the LUT logic; hence, Slices 0 through 3 can be used in ROM mode. Preloading is accomplished through the programming interface during PFU configuration.

For more information, refer to [ECP5 and ECP5-5G Memory Usage Guide \(TN1264\)](#).

2.3. Routing

There are many resources provided in the ECP5/ECP5-5G devices to route signals individually or as busses with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The ECP5/ECP5-5G family has an enhanced routing architecture that produces a compact design. The Diamond design software tool suites take the output of the synthesis tool and places and routes the design.

2.4. Clocking Structure

ECP5/ECP5-5G clocking structure consists of clock synthesis blocks (sysCLOCK PLL); balanced clock tree networks (PCLK and ECLK trees); and efficient clock logic modules (CLOCK DIVIDER and Dynamic Clock Select (DCS), Dynamic Clock Control (DCC) and DLL). All of these functions are described below.

2.4.1. sysCLOCK PLL

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. The devices in the ECP5/ECP5-5G family support two to four full-featured General Purpose PLLs. The sysCLOCK PLLs provide the ability to synthesize clock frequencies.

The architecture of the PLL is shown in [Figure 2.5](#). A description of the PLL functionality follows.

CLKI is the reference frequency input to the PLL and its source can come from two different external CLK inputs or from internal routing. A non-glitchless 2-to-1 input multiplexor is provided to dynamically select between two different external reference clock sources. The CLKI input feeds into the input Clock Divider block.

CLKFB is the feedback signal to the PLL which can come from internal feedback path, routing or an external I/O pin. The feedback divider is used to multiply the reference frequency and thus synthesize a higher frequency clock output.

The PLL has four clock outputs CLKOP, CLKOS, CLKOS2 and CLKOS3. Each output has its own output divider, thus allowing the PLL to generate different frequencies for each output. The output dividers can have a value from 1 to 128. The CLKOP, CLKOS, CLKOS2, and CLKOS3 outputs can all be used to drive the primary clock network. Only CLKOP and CLKOS outputs can go to the edge clock network.

The setup and hold times of the device can be improved by programming a phase shift into the CLKOS, CLKOS2, and CLKOS3 output clocks which will advance or delay the output clock with reference to the CLKOP output clock. This phase shift can be either programmed during configuration or can be adjusted dynamically using the PHASESEL, PHASEDIR, PHASESTEP, and PHASELOADREG ports.

The LOCK signal is asserted when the PLL determines it has achieved lock and de-asserted if a loss of lock is detected.

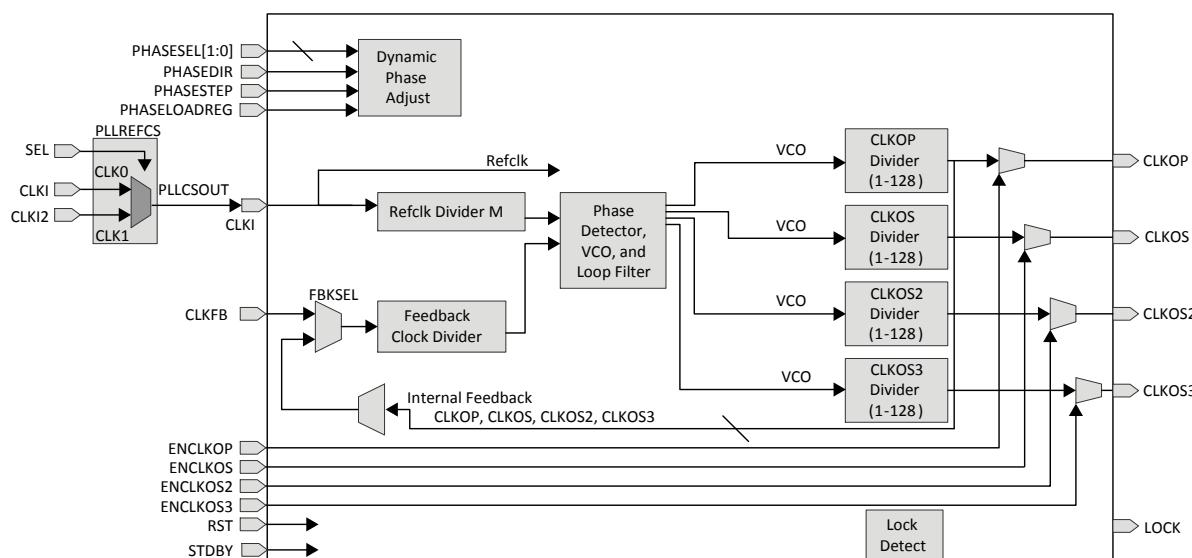


Figure 2.5. General Purpose PLL Diagram

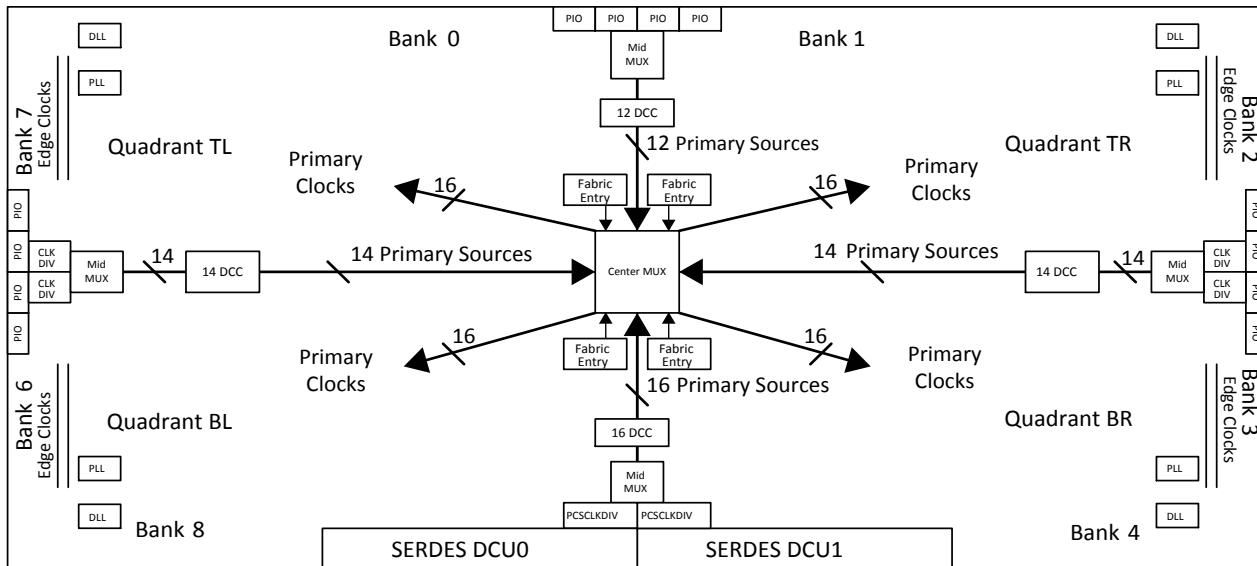


Figure 2.6. LFE5UM/LFE5UM5G-85 Clocking

2.5.1. Primary Clocks

The ECP5/ECP5-5G device family provides low-skew, high fan-out clock distribution to all synchronous elements in the FPGA fabric through the Primary Clock Network.

The primary clock network is divided into four clocking quadrants: Top Left (TL), Bottom Left (BL), Top Right (TR), and Bottom Right (BR). Each of these quadrants has 16 clocks that can be distributed to the fabric in the quadrant.

The Lattice Diamond software can automatically route each clock to one of the four quadrants up to a maximum of 16 clocks per quadrant. The user can change how the clocks are routed by specifying a preference in the Lattice Diamond software to locate the clock to specific. The ECP5/ECP5-5G device provides the user with a maximum of 64 unique clock input sources that can be routed to the primary Clock network.

Primary clock sources are:

- Dedicated clock input pins
- PLL outputs
- CLKDIV outputs
- Internal FPGA fabric entries (with minimum general routing)
- SERDES/PCS/PCSDIV clocks
- OSC clock

These sources are routed to one of four clock switches called a Mid Mux. The outputs of the Mid MUX are routed to the center of the FPGA where another clock switch, called the Center MUX, is used to route the primary clock sources to primary clock distribution to the ECP5/ECP5-5G fabric. These routing muxes are shown in Figure 2.6. Since there is a maximum of 60 unique clock input sources to the clocking quadrants, there are potentially 64 unique clock domains that can be used in the ECP5/ECP5-5G Device. For more information about the primary clock tree and connections, refer to [ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide \(TN1263\)](#).

2.5.1.1. Dynamic Clock Control

The Dynamic Clock Control (DCC) Quadrant Clock enable/disable feature allows internal logic control of the quadrant primary clock network. When a clock network is disabled, the clock signal is static and not toggle. All the logic fed by that clock will not toggle, reducing the overall power consumption of the device. The disable function will not create glitch and increase the clock latency to the primary clock network.

This DCC controls the clock sources from the Primary CLOCK MIDMUX before they are fed to the Primary Center MUX that drive the quadrant clock network. For more information about the DCC, refer to [ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide \(TN1263\)](#).

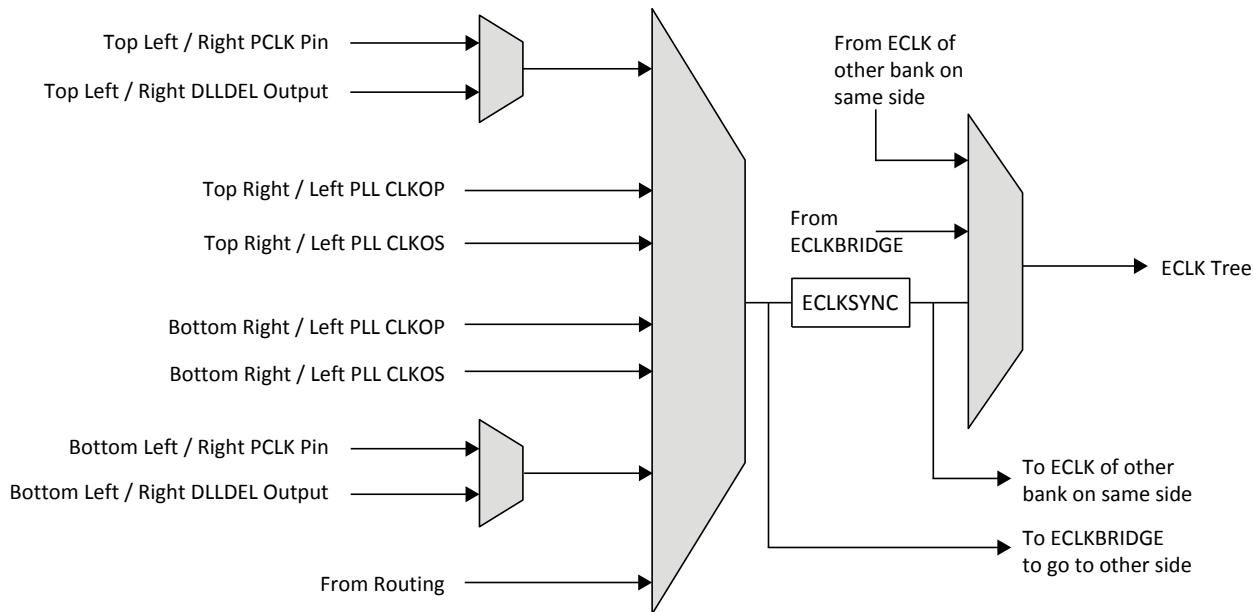


Figure 2.8. Edge Clock Sources per Bank

The edge clocks have low injection delay and low skew. They are used for DDR Memory or Generic DDR interfaces. For detailed information on Edge Clock connections, refer to [ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide \(TN1263\)](#).

2.6. Clock Dividers

ECP5/ECP5-5G devices have two clock dividers, one on the left side and one on the right side of the device. These are intended to generate a slower-speed system clock from a high-speed edge clock. The block operates in a $\div 2$, $\div 3.5$ mode and maintains a known phase relationship between the divided down clock and the high-speed clock based on the release of its reset signal.

The clock dividers can be fed from selected PLL outputs, external primary clock pins multiplexed with the DDRDEL Slave Delay or from routing. The clock divider outputs serve as primary clock sources and feed into the clock distribution network. The Reset (RST) control signal resets input and asynchronously forces all outputs to low. The SLIP signal slips the outputs one cycle relative to the input clock. For further information on clock dividers, refer to [ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide \(TN1263\)](#). Figure 2.9 shows the clock divider connections.

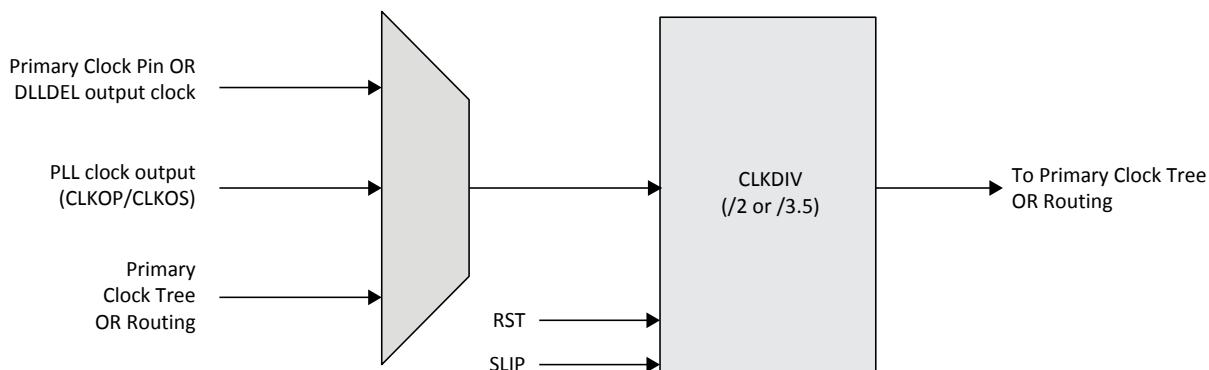
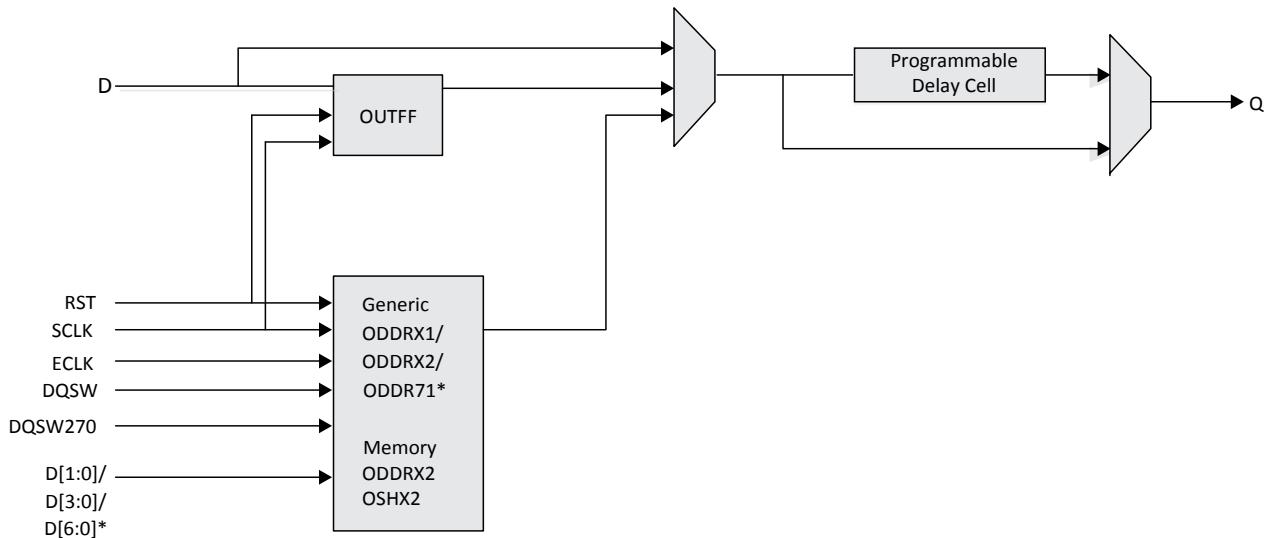


Figure 2.9. ECP5/ECP5-5G Clock Divider Sources



*For 7:1 LVDS interface only. It is required to use PIO pair pins PIOA/B.

Figure 2.20. Output Register Block on Left and Right Sides

Table 2.9. Output Block Port Description

Name	Type	Description
Q	Output	High Speed Data Output
D	Input	Data from core to output SDR register
D[1:0]/D[3:0]/ D[6:0]	Input	Low Speed Data from device core to output DDR register
RST	Input	Reset to the Output Block
SCLK	Input	Slow Speed System Clock
ECLK	Input	High Speed Edge Clock
DQSW	Input	Clock from DQS control Block used to generate DDR memory DQS output
DQSW270	Input	Clock from DQS control Block used to generate DDR memory DQ output

2.12. Tristate Register Block

The tristate register block registers tristate control signals from the core of the device before they are passed to the sysIO buffers. The block contains a register for SDR operation. In SDR, TD input feeds one of the flip-flops that then feeds the output. In DDR operation used mainly for DDR memory interface can be implemented on the left and right sides of the device. Here two inputs feed the tristate registers clocked by both ECLK and SCLK.

Figure 2.21 and Figure 2.22 show the Tristate Register Block functions on the device. For detailed description of the tristate register block modes and usage, refer to [ECP5 and ECP5-5G High-Speed I/O Interface \(TN1265\)](#).

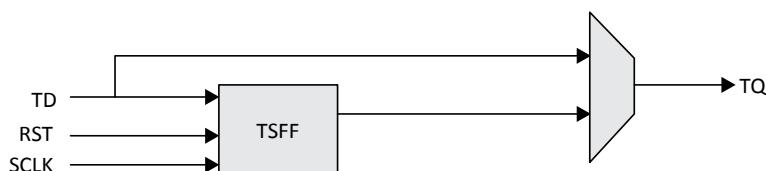


Figure 2.21. Tristate Register Block on Top Side

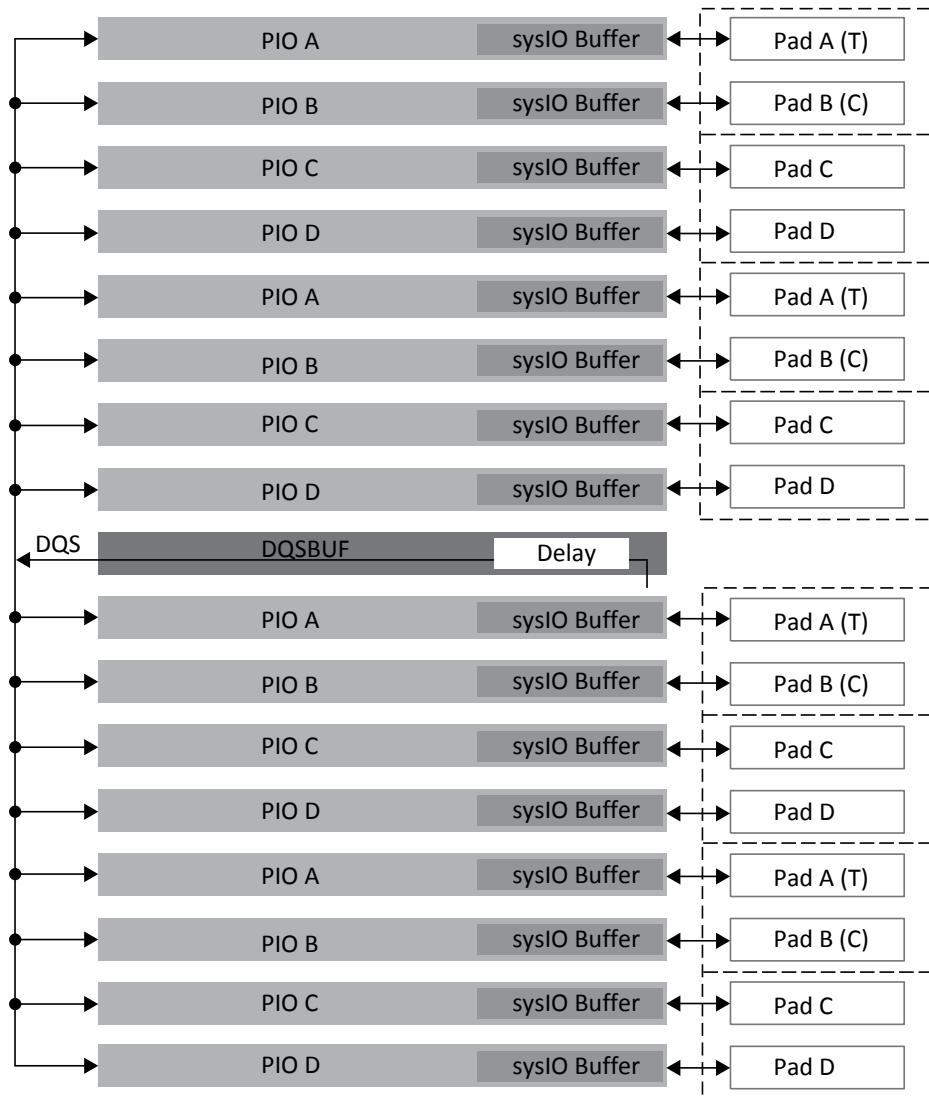


Figure 2.23. DQS Grouping on the Left and Right Edges

2.13.2. DLL Calibrated DQS Delay and Control Block (DQSBUF)

To support DDR memory interfaces (DDR2/3, LPDDR2/3), the DQS strobe signal from the memory must be used to capture the data (DQ) in the PIC registers during memory reads. This signal is output from the DDR memory device aligned to data transitions and must be time shifted before it can be used to capture data in the PIC. This time shifted is achieved by using DQSDEL programmable delay line in the DQS Delay Block (DQS read circuit). The DQSDEL is implemented as a slave delay line and works in conjunction with a master DDRDLL.

This block also includes slave delay line to generate delayed clocks used in the write side to generate DQ and DQS with correct phases within one DQS group. There is a third delay line inside this block used to provide write leveling feature for DDR write if needed.

Each of the read and write side delays can be dynamically shifted using margin control signals that can be controlled by the core logic.

FIFO Control Block shown in Figure 2.24 generates the Read and Write Pointers for the FIFO block inside the Input Register Block. These pointers are generated to control the DQS to ECLK domain crossing using the FIFO module.

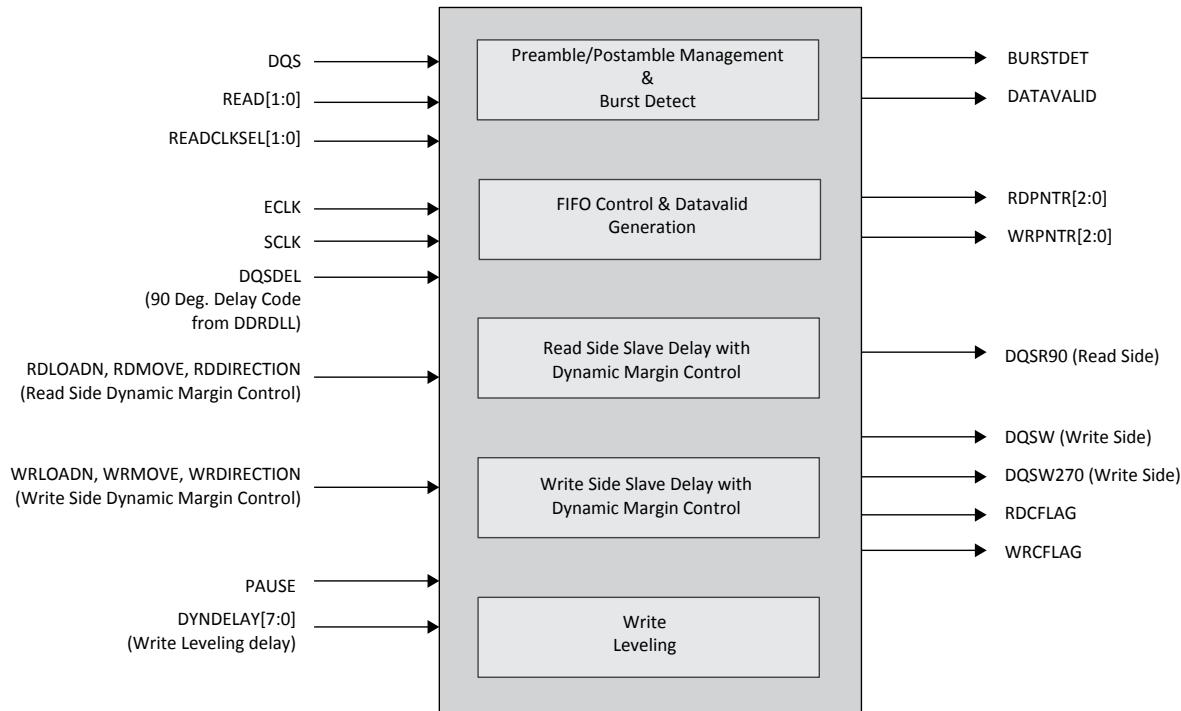


Figure 2.24. DQS Control and Delay Block (DQSBUF)

Table 2.11. DQSBUF Port List Description

Name	Type	Description
DQS	Input	DDR memory DQS strobe
READ[1:0]	Input	Read Input from DDR Controller
READCLKSEL[1:0]	Input	Read pulse selection
SCLK	Input	Slow System Clock
ECLK	Input	High Speed Edge Clock (same frequency as DDR memory)
DQSDEL	Input	90° Delay Code from DDRDLL
RDLOADN, RDMOVE, RDDIRECTION	Input	Dynamic Margin Control ports for Read delay
WRLOADN, WRMOVE, WRDIRECTION	Input	Dynamic Margin Control ports for Write delay
PAUSE	Input	Used by DDR Controller to Pause write side signals during DDRDLL Code update or Write Leveling
DYNDELAY[7:0]	Input	Dynamic Write Leveling Delay Control
DQSR90	Output	90° delay DQS used for Read
DQSW270	Output	90° delay clock used for DQ Write
DQSW	Output	Clock used for DQS Write
RDPNTR[2:0]	Output	Read Pointer for IFIFO module
WRPNTR[2:0]	Output	Write Pointer for IFIFO module
DATAVALID	Output	Signal indicating start of valid data
BURSTDET	Output	Burst Detect indicator
RDFLAG	Output	Read Dynamic Margin Control output to indicate max value
WRFLAG	Output	Write Dynamic Margin Control output to indicate max value

2.14.4. On-Chip Programmable Termination

The ECP5/ECP5-5G devices support a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of $50\ \Omega$, $75\ \Omega$, or $150\ \Omega$.
- Common mode termination of $100\ \Omega$ for differential inputs.

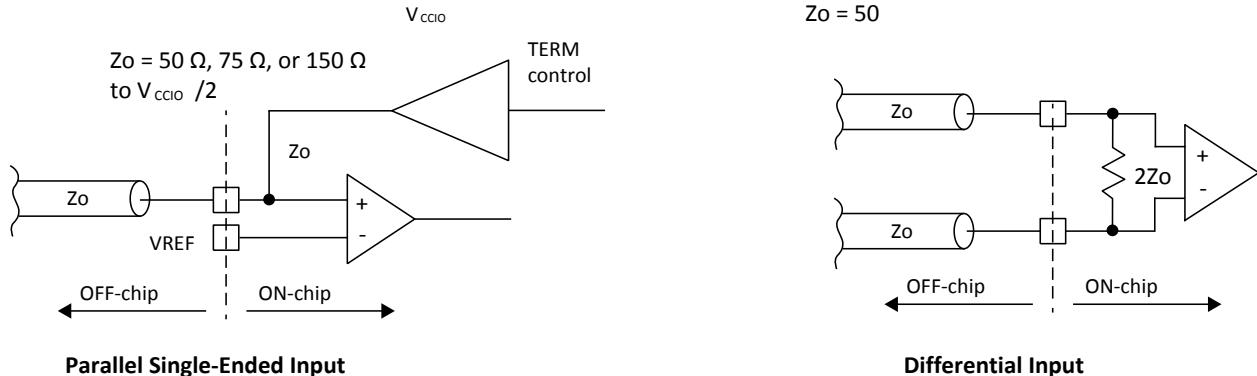


Figure 2.26. On-Chip Termination

See [Table 2.12](#) for termination options for input modes.

Table 2.12. On-Chip Termination Options for Input Modes

IO_TYPE	Terminate to $V_{CCIO}/2^*$	Differential Termination Resistor*
LVDS25	—	100
BLVDS25	—	100
MLVDS	—	100
LVPECL33	—	100
subLVDS	—	100
SLVS	—	100
HSUL12	50, 75, 150	—
HSUL12D	—	100
SSTL135_I / II	50, 75, 150	—
SSTL135D_I / II	—	100
SSTL15_I / II	50, 75, 150	—
SSTL15D_I / II	—	100
SSTL18_I / II	50, 75, 150	—
SSTL18D_I / II	—	100

*Notes:

TERMINATE to $V_{CCIO}/2$ (Single-Ended) and DIFFERENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.

Use of TERMINATE to $V_{CCIO}/2$ and DIFFERENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank. On-chip termination tolerance $\pm 20\%$.

Refer to [ECP5 and ECP5-5G sysIO Usage Guide \(TN1262\)](#) for on-chip termination usage and value ranges.

2.14.5. Hot Socketing

ECP5/ECP5-5G devices have been carefully designed to ensure predictable behavior during power-up and power-down. During power-up and power-down sequences, the I/Os remain in tristate until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. See the [Hot Socketing Specifications](#) section on page 48.

3.7. Hot Socketing Requirements

Table 3.6. Hot Socketing Requirements

Description	Min	Typ	Max	Unit
Input current per SERDES I/O pin when device is powered down and inputs driven.	—	—	8	mA
Input current per HDIN pin when device power supply is off, inputs driven ^{1, 2}	—	—	15	mA
Current per HDIN pin when device power ramps up, input driven ³	—	—	50	mA
Current per HDOUT pin when device power supply is off, outputs pulled up ⁴	—	—	30	mA

Notes:

1. Device is powered down with all supplies grounded, both HDINP and HDINN inputs driven by a CML driver with maximum allowed output V_{CCHTX} , 8b/10b data, no external AC coupling.
2. Each P and N input must have less than the specified maximum input current during hot plug. For a device with 2 DCU, the total input current would be $15\text{ mA} * 4\text{ channels} * 2\text{ input pins per channel} = 120\text{ mA}$.
3. Device power supplies are ramping up (V_{CCA} and V_{CCAUX}), both HDINP and HDINN inputs are driven by a CML driver with maximum allowed output V_{CCHTX} , 8b/10b data, internal AC coupling.
4. Device is powered down with all supplies grounded. Both HDOUTP and HDOUN outputs are pulled up to V_{CCHTX} by the far end receiver termination of $50\text{ }\Omega$ single ended.

3.8. ESD Performance

Refer to the [ECP5 and ECP5-5G Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

3.9. DC Electrical Characteristics

Over Recommended Operating Conditions

Table 3.7. DC Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$I_{IL}, I_{IH}^{1, 4}$	Input or I/O Low Leakage	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	10	μA
$I_{IH}^{1, 3}$	Input or I/O High Leakage	$V_{CCIO} < V_{IN} \leq V_{IH(\text{MAX})}$	—	—	100	μA
I_{PU}	I/O Active Pull-up Current, sustaining logic HIGH state	$0.7 V_{CCIO} \leq V_{IN} \leq V_{CCIO}$	-30	—	—	μA
	I/O Active Pull-up Current, pulling down from logic HIGH state	$0 \leq V_{IN} \leq 0.7 V_{CCIO}$	—	—	-150	μA
I_{PD}	I/O Active Pull-down Current, sustaining logic LOW state	$0 \leq V_{IN} \leq V_{IL(\text{MAX})}$	30	—	—	μA
	I/O Active Pull-down Current, pulling up from logic LOW state	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	150	μA
C1	I/O Capacitance ²	$V_{CCIO} = 3.3\text{ V}, 2.5\text{ V}, 1.8\text{ V}, 1.5\text{ V}, 1.2\text{ V}$, $V_{CC} = 1.2\text{ V}$, $V_{IO} = 0$ to $V_{IH(\text{MAX})}$	—	5	8	pf
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3\text{ V}, 2.5\text{ V}, 1.8\text{ V}, 1.5\text{ V}, 1.2\text{ V}$, $V_{CC} = 1.2\text{ V}$, $V_{IO} = 0$ to $V_{IH(\text{MAX})}$	—	5	7	pf
V_{HYST}	Hysteresis for Single-Ended Inputs	$V_{CCIO} = 3.3\text{ V}$	—	300	—	mV
		$V_{CCIO} = 2.5\text{ V}$	—	250	—	mV

Notes:

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tristated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. $T_A 25^\circ\text{C}$, $f = 1.0\text{ MHz}$.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF} , maximum leakage= $25\text{ }\mu\text{A}$.

Table 3.10. ECP5-5G

Symbol	Description	Typ	Max	Unit
Standby (Power Down)				
I _{CCA-SB}	V _{CCA} Power Supply Current (Per Channel)	4	9.5	mA
I _{CCHRX-SB} ⁴	V _{CCHRX} , Input Buffer Current (Per Channel)	—	0.1	mA
I _{CCHTX-SB}	V _{CCHTX} , Output Buffer Current (Per Channel)	—	0.9	mA
Operating (Data Rate = 5 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	58	67	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 3.2 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	48	57	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 2.5 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	44	53	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 1.25 Gb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	36	46	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	10	13	mA
Operating (Data Rate = 270 Mb/s)				
I _{CCA-OP}	V _{CCA} Power Supply Current (Per Channel)	30	40	mA
I _{CCHRX-OP} ⁵	V _{CCHRX} , Input Buffer Current (Per Channel)	0.4	0.5	mA
I _{CCHTX-OP}	V _{CCHTX} , Output Buffer Current (Per Channel)	8	10	mA

Notes:

1. Rx Equalization enabled, Tx De-emphasis (pre-cursor and post-cursor) disabled
2. Per Channel current is calculated with both channels on in a Dual, and divide current by two. If only one channel is on, current will be higher.
3. To calculate with Tx De-emphasis enabled, use the Diamond Power Calculator tool.
4. For I_{CCHRX-SB}, during Standby, input termination on Rx are disabled.
5. For I_{CCHRX-OP}, during operational, the max specified when external AC coupling is used. If externally DC coupled, the power is based on current pulled down by external driver when the input is driven to LOW.

3.15. Typical Building Block Function Performance

Table 3.19. Pin-to-Pin Performance

Function	-8 Timing	Unit
Basic Functions		
16-Bit Decoder	5.06	ns
32-Bit Decoder	6.08	ns
64-Bit Decoder	5.06	ns
4:1 Mux	4.45	ns
8:1 Mux	4.63	ns
16:1 Mux	4.81	ns
32:1 Mux	4.85	ns

Notes:

1. I/Os are configured with LVC MOS25 with $V_{COO}=2.5$, 12 mA drive.
2. These functions were generated using Lattice Diamond design software tool. Exact performance may vary with the device and the design software tool version. The design software tool uses internal parameters that have been characterized but are not tested on every device.
3. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from Lattice Diamond design software tool.

3.17. Maximum I/O Buffer Speed

Over recommended operating conditions.

Table 3.21. ECP5/ECP5-5G Maximum I/O Buffer Speed

Buffer	Description	Max	Unit
Maximum Input Frequency			
LVDS25	LVDS, $V_{CCIO} = 2.5$ V	400	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5$ V	400	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5$ V	400	MHz
MIPI D-PHY (HS Mode)	MIPI Video	400	MHz
SLVS	SLVS similar to MIPI	400	MHz
Mini LVDS	Mini LVDS	400	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3$ V	400	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8$ V	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, $V_{CCIO} = 1.5$ V	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, $V_{CCIO} = 1.35$ V	400	MHz
HSUL12 (all supported classes)	HSUL_12 class I, II, $V_{CCIO} = 1.2$ V	400	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3$ V	200	MHz
LVCMOS33	LVCMOS, $V_{CCIO} = 3.3$ V	200	MHz
LVCMOS25	LVCMOS, $V_{CCIO} = 2.5$ V	200	MHz
LVCMOS18	LVCMOS, $V_{CCIO} = 1.8$ V	200	MHz
LVCMOS15	LVCMOS 1.5, $V_{CCIO} = 1.5$ V	200	MHz
LVCMOS12	LVCMOS 1.2, $V_{CCIO} = 1.2$ V	200	MHz
Maximum Output Frequency			
LVDS25E	LVDS, Emulated, $V_{CCIO} = 2.5$ V	150	MHz
LVDS25	LVDS, $V_{CCIO} = 2.5$ V	400	MHz
MLVDS25	MLVDS, Emulated, $V_{CCIO} = 2.5$ V	150	MHz
BLVDS25	BLVDS, Emulated, $V_{CCIO} = 2.5$ V	150	MHz
LVPECL33	LVPECL, Emulated, $V_{CCIO} = 3.3$ V	150	MHz
SSTL18 (all supported classes)	SSTL_18 class I, II, $V_{CCIO} = 1.8$ V	400	MHz
SSTL15 (all supported classes)	SSTL_15 class I, II, $V_{CCIO} = 1.5$ V	400	MHz
SSTL135 (all supported classes)	SSTL_135 class I, II, $V_{CCIO} = 1.35$ V	400	MHz
HSUL12 (all supported classes)	HSUL12 class I, II, $V_{CCIO} = 1.2$ V	400	MHz
LVTTL33	LVTTL, $V_{CCIO} = 3.3$ V	150	MHz
LVCMOS33 (For all drives)	LVCMOS, 3.3 V	150	MHz
LVCMOS25 (For all drives)	LVCMOS, 2.5 V	150	MHz
LVCMOS18 (For all drives)	LVCMOS, 1.8 V	150	MHz
LVCMOS15 (For all drives)	LVCMOS, 1.5 V	150	MHz
LVCMOS12 (For all drives)	LVCMOS, 1.2 V	150	MHz

Notes:

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVCMOS timing is measured with the load specified in Switching Test Conditions, Table 3.44 on page 90.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

3.19. sysCLOCK PLL Timing

Over recommended operating conditions.

Table 3.23. sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Min	Max	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)	—	8	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)	—	3.125	400	MHz
f_{VCO}	PLL VCO Frequency	—	400	800	MHz
f_{PFD}^3	Phase Detector Input Frequency	—	10	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	—	45	55	%
t_{PH4}	Output Phase Accuracy	—	-5	5	%
t_{OPJIT}^1	Output Clock Period Jitter	$f_{OUT} \geq 100$ MHz	—	100	ps p-p
		$f_{OUT} < 100$ MHz	—	0.025	UIPP
	Output Clock Cycle-to-Cycle Jitter	$f_{OUT} \geq 100$ MHz	—	200	ps p-p
		$f_{OUT} < 100$ MHz	—	0.050	UIPP
	Output Clock Phase Jitter	$f_{PFD} \geq 100$ MHz	—	200	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	—	400	ps p-p
t_w	Output Clock Pulse Width	At 90% or 10%	0.9	—	ns
t_{LOCK}^2	PLL Lock-in Time	—	—	15	ms
t_{UNLOCK}	PLL Unlock Time	—	—	50	ns
t_{IPJIT}	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{RST}	RST / Pulse Width	—	1	—	ms
t_{RSTREC}	RST Recovery Time	—	1	—	ns
t_{LOAD_REG}	Min Pulse for CIB_LOAD_REG	—	10	—	ns
$t_{ROTATE-SETUP}$	Min time for CIB dynamic phase controls to be stable before CIB_ROTATE	—	5	—	ns
$t_{ROTATE-WD}$	Min pulse width for CIB_ROTATE to maintain "0" or	—	4	—	VCO cycles

Notes:

1. Jitter sample is taken over 10,000 samples for Periodic jitter, and 2,000 samples for Cycle-to-Cycle jitter of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 10$ MHz. For $f_{PFD} < 10$ MHz, the jitter numbers may not be met in certain conditions.

3.22. SERDES High-Speed Data Receiver

Table 3.27. Serial Input Data Specifications

Symbol	Description	Min	Typ	Max	Unit
$V_{RX-DIFF-S}$	Differential input sensitivity	150	—	1760	mV, p-p
V_{RX-IN}	Input levels	0	—	$V_{CCA} + 0.5^2$	V
$V_{RX-CM-DCCM}$	Input common mode range (internal DC coupled mode)	0.6	—	V_{CCA}	V
$V_{RX-CM-ACCM}$	Input common mode range (internal AC coupled mode) ²	0.1	—	$V_{CCA} + 0.2$	V
$T_{RX-RELOCK}$	SCDR re-lock time ¹	—	1000	—	Bits
$Z_{RX-TERM}$	Input termination 50/75 Ω /High Z	-20%	50/75/5 K	+20%	Ω
RL_{RX-RL}	Return loss (without package)	—	—	-10	dB

Notes:

1. This is the typical number of bit times to re-lock to a new phase or frequency within ±300 ppm, assuming 8b10b encoded data.
2. Up to 1.655 for ECP5, and 1.76 for ECP5-5G.

3.23. Input Data Jitter Tolerance

A receiver's ability to tolerate incoming signal jitter is very dependent on jitter type. High speed serial interface standards have recognized the dependency on jitter type and have specifications to indicate tolerance levels for different jitter types as they relate to specific protocols. Sinusoidal jitter is considered to be a worst case jitter type.

Table 3.28. Receiver Total Jitter Tolerance Specification

Description	Frequency	Condition	Min	Typ	Max	Unit
Deterministic	5 Gb/s	400 mV differential eye	—	—	TBD	UI, p-p
Random		400 mV differential eye	—	—	TBD	UI, p-p
Total		400 mV differential eye	—	—	TBD	UI, p-p
Deterministic	3.125 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p
Deterministic	2.5 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p
Deterministic	1.25 Gb/s	400 mV differential eye	—	—	0.37	UI, p-p
Random		400 mV differential eye	—	—	0.18	UI, p-p
Total		400 mV differential eye	—	—	0.65	UI, p-p

Notes:

1. Jitter tolerance measurements are done with protocol compliance tests: 3.125 Gb/s - XAU1 Standard, 2.5 Gb/s - PCIe Standard, 1.25 Gb/s - SGMII Standard.
2. For ECP5-5G family devices only.

Table 3.36. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL_RX_DIFF	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL_RX_CM	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z_RX_DIFF	Differential termination resistance	—	80	100	120	Ω
J_RX_DJ ^{2, 3, 4}	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.37	UI
J_RX_RJ ^{2, 3, 4}	Random jitter tolerance (peak-to-peak)	—	—	—	0.18	UI
J_RX_SJ ^{2, 3, 4}	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.10	UI
J_RX_TJ ^{1, 2, 3, 4}	Total jitter tolerance (peak-to-peak)	—	—	—	0.65	UI
T_RX_EYE	Receiver eye opening	—	0.35	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.

3.29. Gigabit Ethernet/SGMII(1.25Gbps)/CPRI LV E.12 Electrical and Timing Characteristics

3.29.1. AC and DC Characteristics

Table 3.37. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T _{RF}	Differential rise/fall time	20% to 80%	—	80	—	ps
Z _{TX_DIFF_DC}	Differential impedance	—	80	100	120	Ω
J _{TX_DDJ} ^{2, 3}	Output data deterministic jitter	—	—	—	0.10	UI
J _{TX_TJ} ^{1, 2, 3}	Total output data jitter	—	—	—	0.24	UI

Notes:

1. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
2. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Table 3.38. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL_RX_DIFF	Differential return loss	From 100 MHz to 1.25 GHz	10	—	—	dB
RL_RX_CM	Common mode return loss	From 100 MHz to 1.25 GHz	6	—	—	dB
Z_RX_DIFF	Differential termination resistance	—	80	100	120	Ω
J_RX_DJ ^{1, 2, 3, 4}	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.34	UI
J_RX_RJ ^{1, 2, 3, 4}	Random jitter tolerance (peak-to-peak)	—	—	—	0.26	UI
J_RX_SJ ^{1, 2, 3, 4}	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.11	UI
J_RX_TJ ^{1, 2, 3, 4}	Total jitter tolerance (peak-to-peak)	—	—	—	0.71	UI
T_RX_EYE	Receiver eye opening	—	0.29	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.

3.30. SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

3.30.1. AC and DC Characteristics

Table 3.39. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
BR _{SDO}	Serial data rate	—	270	—	2975	Mb/s
T _{JALIGNMENT} ²	Serial output jitter, alignment	270 Mb/s ⁶	—	—	0.2	UI
T _{JALIGNMENT} ²	Serial output jitter, alignment	1485 Mb/s	—	—	0.2	UI
T _{JALIGNMENT} ^{1, 2}	Serial output jitter, alignment	2970 Mb/s	—	—	0.3	UI
T _{JTIMING}	Serial output jitter, timing	270 Mb/s ⁶	—	—	0.2	UI
T _{JTIMING}	Serial output jitter, timing	1485 Mb/s	—	—	1	UI
T _{JTIMING}	Serial output jitter, timing	2970 Mb/s	—	—	2	UI

Notes:

1. Timing jitter is measured in accordance with SMPTE serial data transmission standards.
2. Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
3. All Tx jitter are measured at the output of an industry standard cable driver, with the Lattice SERDES device configured to 50 Ω output impedance connecting to the external cable driver with differential signaling.
4. The cable driver drives: RL=75 Ω, AC-coupled at 270, 1485, or 2970 Mb/s.
5. All LFE5UM/LFE5UM5G devices are compliant with all SMPTE compliance tests, except 3G-SDI Level-A pathological compliance pattern test.
6. 270 Mb/s is supported with Rate Divider only.

Table 3.40. Receive

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
BR _{SDI}	Serial input data rate	—	270	—	2970	Mb/s

Table 3.41. Reference Clock

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
F _{VCLK}	Video output clock frequency	—	54	—	148.5	MHz
DC _V	Duty cycle, video clock	—	45	50	55	%

Note: SD-SDI (270 Mb/s) is supported with Rate Divider only. For Single Rate: Reference Clock = 54 MHz and Rate Divider = /2. For Tri-Rate: Reference Clock = 148.5 MHz and Rate Divider = /11.

(Continued)

Date	Version	Section	Change Summary
April 2017	1.7	All	Changed document number from DS1044 to FPGA-DS-02012.
		General Description	Updated Features section. Changed “1.1 V core power supply” to “1.1 V core power supply for ECP5, 1.2 V core power supply for ECP5UM5G”.
		Architecture	Updated Overview section. Change “The ECP5/ECP5-5G devices use 1.1 V as their core voltage” to “The ECP5 devices use 1.1V, ECP5UM5G devices use 1.2V as their core voltage”
		DC and Switching Characteristics	Updated Table 3.2. Recommended Operating Conditions Added ECP5-5G on VCC to be 1.2V +/- 5% Added ECP5-5G on VCCA to be 1.2V +/- 3% Updated Table 3.8. ECP5/ECP5-5G Supply Current (Standby) Changed “Core Power Supply Current” for ICC on LFE5UM5G devices Changed “SERDES Power Supply Current (Per Dual)” for ICCA on LFE5UM5G devices Updated Table 3.20. Register-to-Register Performance. Remove “(DDR/SDR)” from DSP Function Changed DSP functions to 225 MHz
		Pinout Information	Update Section 4.1 Signal Description. Revised Vcc Description to “Power supply pins for core logic. Dedicated pins. VCC = 1.1 V (ECP5), 1.2 V (ECP5UM5G)”
February 2016	1.6	All	Changed document status from Preliminary to Final.
		General Description	Updated Features section. Changed “24K to 84K LUTs” to “12K to 84K LUTs”. Added LFE5U-12 column to Table 1.1. ECP5 and ECP5-5G Family Selection Guide.
		DC and Switching Characteristics	Updated Power up Sequence section. Identified typical ICC current for specific devices in Table 3.8. ECP5/ECP5-5G Supply Current (Standby). Updated values in Table 3.9. ECP5. Updated values in Table 3.10. ECP5-5G. Added values to -8 Timing column of Table 3.19. Pin-to-Pin Performance. Added values to -8 Timing column of Table 3.20. Register-to-Register Performance. Changed LFE5-45 to All Devices in Table 3.22. ECP5/ECP5-5G External Switching Characteristics. Added table notes to Table 3.31. PCIe (5 Gb/s). Added table note to Table 3.32. CPRI LV2 E.48 Electrical and Timing Characteristics.
		Pinout Information	Added LFE5U-12 column to the table in LFE5U section.
		Ordering Information	Updated LFE5U in ECP5/ECP5-5G Part Number Description section: added 12 F = 12K LUTs to Logic Capacity. Added LFE5U-12F information to Ordering Part Numbers section.

(Continued)

Date	Version	Section	Change Summary
August 2014	1.2	DC and Switching Characteristics	SERDES High-Speed Data Receiver section. Updated Table 3.26. Serial Input Data Specifications, Table 3.28. Receiver Total Jitter Tolerance Specification, and Table 3.29. External Reference Clock Specification (refclkp/refclkn).
			Modified section heading to XXAUI/CPRI LV E.30 Electrical and Timing Characteristics. Updated Table 3.33 Transmit and Table 3.34. Receive and Jitter Tolerance.
			Modified section heading to CPRI LV E.24 Electrical and Timing Characteristics. Updated Table 3.35. Transmit and Table 3.36. Receive and Jitter Tolerance.
			Modified section heading to Gigabit Ethernet/SGMII/CPRI LV E.12 Electrical and Timing Characteristics. Updated Table 3.37. Transmit and Table 3.38. Receive and Jitter Tolerance.
June 2014	1.1	Ordering Information	Updated ECP5/ECP5-5G Part Number Description and Ordering Part Numbers sections.
March 2014	1.0	All	Initial release.